# **PIN Silicon Photodiode**

# OP905, OP906



#### Features:

- Clear epoxy package
- Linear response vs. irradiance
- Fast switching time
- · Narrow receiving angle
- T-1 package style
- Small package style ideal for space-limited applications



## **Description:**

Each **OP905** and **OP906** device consists of a PIN silicon photodiode molded in a clear polysulfone package that allows spectral response from visible to infrared light wavelengths. The T-1 package style is ideal for space-limited applications. Both devices have a narrow receiving angle, which provides excellent on-axis coupling. Both are also 100% production tested using infrared light for close correlation with OPTEK's GaAs and GaAlAs emitters.

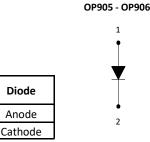
Please refer to Application Bulletin 210 for additional thermal design information.

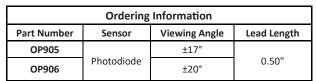
## **Applications:**

- Non-contact reflective object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor

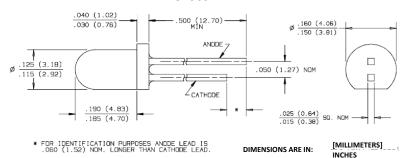
Pin#

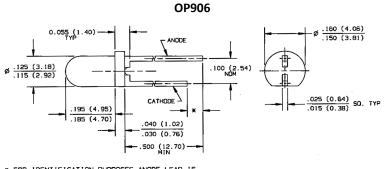
2





#### OP905





Pb

▼ FOR IDENTIFICATION PURPOSES ANODE LEAD IS .060 (1.52) NOM. LONGER THAN CATHODE LEAD.

DIMENSIONS ARE IN INCHES (MILLIMETERS)

#### **CONTAINS POLYSULFONE**

To avoid stress cracking, we suggest using ND Industries' **Vibra-Tite** for thread-locking. **Vibra-Tite** evaporates fast without causing structural failure in OPTEK'S molded plastics.

General Note

TT Electronics | OPTEK Technology 2900 E. Plano Pkwy, Plano, TX 75074 | Ph: +1 972 323 2200 www.ttelectronics.com | sensors@ttelectronics.com OP905, OP906



# **Electrical Specifications**

## Absolute Maximum Ratings (T<sub>A</sub> = 25° C unless otherwise noted)

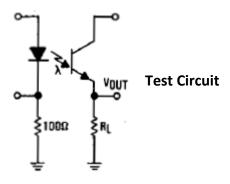
Reverse Breakdown Voltage	60 V
Storage & Operating Temperature Range	-40° C to +100° C
Lead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 sec. with soldering iron] (1)	260° C
Reverse Breakdown Voltage	60 V
Power Dissipation <sup>(2)</sup>	100 mW

## Electrical Characteristics (T<sub>A</sub> = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
I <sub>L</sub> <sup>(3)</sup>	Reverse Light Current OP905 OP906	14 16	-	32 35	μΑ	$V_R = 5 \text{ V}, E_E = 0.50 \text{ mW/cm}^2$
I <sub>D</sub> <sup>(4)</sup>	Reverse Dark Current	-	1	60	nA	$V_R = 30 \text{ V}, E_E = 0$
$V_{(BR)}$	Reverse Breakdown Voltage	60	-	-	V	Ι <sub>R</sub> = 100 μΑ
$V_{F}$	Forward Voltage	-	-	1.2	٧	I <sub>F</sub> = 1 mA
C <sub>T</sub>	Total Capacitance	-	4	-	pF	V <sub>R</sub> = 20 V, E <sub>E</sub> = 0, f = 1.0 MHz
t <sub>r</sub>	Rise Time	-	5	-	nc	$V_R = 20 \text{ V}, \lambda = 850 \text{ nm}, R_L = 50 \Omega$
t <sub>f</sub>	Fall Time	-	5	-	ns	V <sub>R</sub> - 20 V, Λ - 650 IIII, K <sub>L</sub> = 50 Ω

#### Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum of 20 grams force may be applied to leads when soldering.
- (2) Derate linearly 1.07 mW/° C above 25° C.
- (3) Light source is an unfiltered GaAs LED with a peak emission wavelength of 935 nm and a radiometric intensity level which varies less than 10% over the entire lens surface of the photodiode being tested. (4) Calculate the typical dark current in nA using the formula  $I_D = 10^{(0.042T_A^{-1.5})}$  where  $T_A$  is ambient temperature in °C.

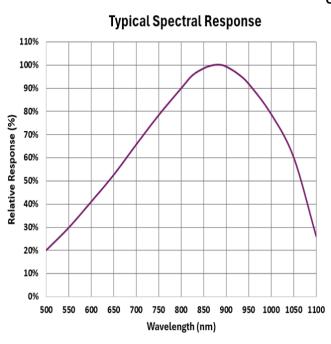


# **PIN Silicon Photodiode**

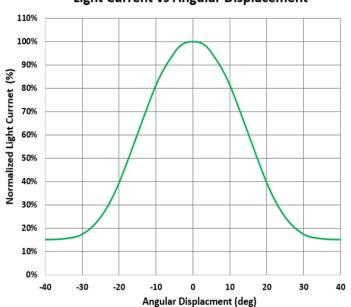
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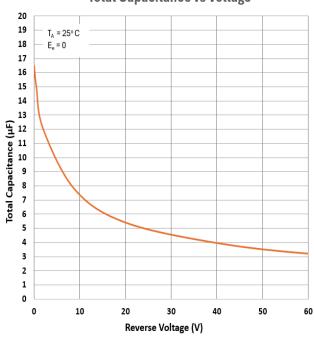
# Typical Performance OP905



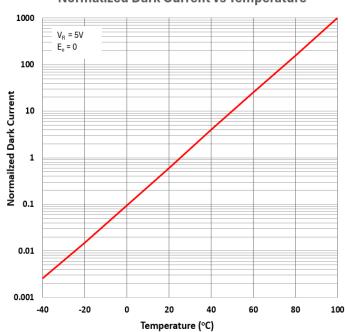
# **Light Current vs Angular Displacement**



# **Total Capacitance vs Voltage**



## **Normalized Dark Current vs Temperature**

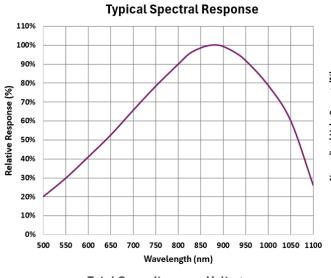


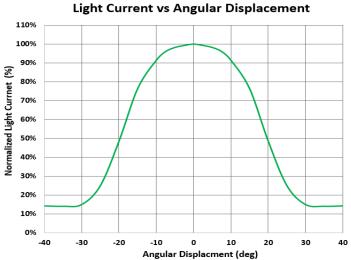
OP905, OP906



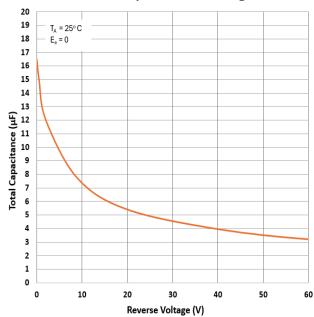
# **Typical Performance**

**OP906** 





### **Total Capacitance vs Voltage**



## **Normalized Dark Current vs Temperature**

